

CLAIMS

1. A polishing slurry for semiconductor planarization containing cerium oxide particles and water, wherein the content of the cerium oxide particles having a diameter of at least 3 μm is not more than 500 ppm in a solid.

2. The polishing slurry for semiconductor planarization according to claim 1, further containing a dispersing agent.

3. The polishing slurry for semiconductor planarization according to claim 1 or 2, wherein the particle diameter is not more than 1 μm in 99 % by volume of the whole cerium oxide particles.